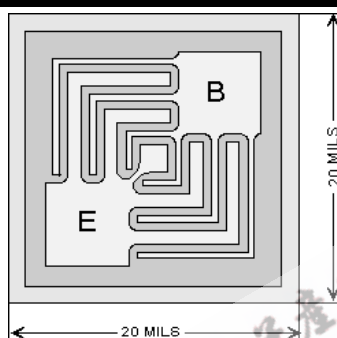


Chip Type 2C2907A
Geometry 0600
Polarity PNP

Generic Packaged Parts:
2N2905, 2N2905A, 2N2907,
2N2907A



[Request Quotation](#)

Chip type **2C2907A** by Semicoa Semiconductors provides performance similar to these devices.

Part Numbers:

[2N2905](#), [2N2905A](#), [2N2905AL](#), [2N2907](#), [2N2907A](#),
[2N2907AUB](#), [SD2907A](#), [SD2907AF](#), [SQ2907A](#),
[SQ2907AF](#), [2N3486](#), [2N3486A](#), [2N6987](#), [2N6989](#)

Product Summary:

APPLICATIONS: Designed for general purpose switching and amplifier applications.

Features: [Radiation graphs available](#)

Mechanical Specifications

Metallization	Top	Al - 18 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	4.0 mils x 4.0 mils
	Base	4.0 mils x 4.0 mils
Die Thickness	8 mils nominal	
Chip Area	20 mils x 20 mils	
Top Surface	Silox Passivated	

Electrical Characteristics

$T_A = 25^\circ\text{C}$

Parameter	Test conditions	Min	Max	Unit
BV_{CEO}	$I_C = 10 \text{ mA}$, $I_B = 0$	60	---	V dc
BV_{CBO}	$I_C = 10 \text{ }\mu\text{A}$, $I_E = 0$	60	---	V dc
BV_{EBO}	$I_E = 10 \text{ }\mu\text{A}$, $I_C = 0$	5.0	---	V dc
I_{CBO}	$V_{CB} = 50 \text{ V}$, $I_E = 0$	---	10	nA
h_{FE}	$I_C = 150 \text{ mA dc}$, $V_{CE} = 10 \text{ V}$	100	300	---

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 μs , duty cycle less than 2%.